

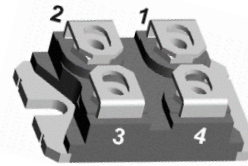
HCD5G120120P Silicon Carbide Schottky Diode

$$V_{RRM} = 1200V$$

$$I_F(T_C=153^{\circ}C) = 120 A$$

$$Q_C = 450 nC$$

Package : SOT-227



Features

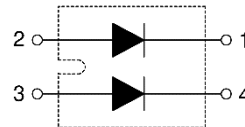
- 1200 V Schottky Rectifier
- Zero Reverse Recovery Current
- High-Frequency Operation
- Temperature-Independent Switching
- Extremely Fast Switching

Benefits

- Replace Bipolar with Unipolar Rectifiers
- Essentially No Switching Losses
- High Efficiency
- Reduction of Heat Sink Requirements
- Parallel Devices Without Thermal Runaway

Applications

- Switching Mode Power Supply
- Boost Diodes in PFC
- DC/DC Converters
- AC/DC Converters
- Free Wheeling Diodes in Inverter



Part Number	Package	Marking
HCD5G120120P	SOT-227	HCD5G120120P

Maximum Ratings $T_c = 25^{\circ}C$ (unless otherwise specified)

Symbol	Parameter	Value	Unit	Test Conditions	Note
V_{RRM}	Repetitive Peak Reverse Voltage	1200	V		
V_{RSM}	Surge Peak Reverse Voltage	1300	V		
V_R	DC Peak Reverse Voltage	1200	V		
I_F	Continuous Forward Current	97 77 60	A	$T_c=25^{\circ}C$ $T_c=75^{\circ}C$ $T_c=108^{\circ}C$	Fig. 3
I_{FSM}	Non- Repetitive Forward Surge Current	380	A	$T_c=25^{\circ}C$, $t_p=10$ ms, Half Sine Pulse	
P_{tot}	Power Dissipation	330 145	W	$T_c=25^{\circ}C$ $T_c=110^{\circ}C$	Fig. 4
T_J	Operating Junction Range	-55 to +175	$^{\circ}C$		
T_{stg}	Storage Temperature Range	-55 to +175	$^{\circ}C$		

Electrical Characteristics

Symbol	Parameter	Typ.	Max.	Unit	Test Conditions	Note
V_F	Forward Voltage	1.65 2.5	1.9 3.0	V	$I_F = 60A, T_J = 25^\circ C$ $I_F = 60A, T_J = 175^\circ C$	Fig. 1
I_R	Reverse Current	25 150	100 800	μA	$V_R = 1200V, T_J = 25^\circ C$ $V_R = 1200V, T_J = 175^\circ C$	Fig. 2
Q_C	Total Capacitive Charge	450		nC	$V_R = 800V, I_F = 60A,$ $T_J = 25^\circ C$	Fig. 6
C	Total Capacitance	10747 349 298		pF	$V_R = 0V, T_J = 25^\circ C, f = 1\text{ MHz}$ $V_R = 400V, T_J = 25^\circ C, f = 1\text{ MHz}$ $V_R = 800V, T_J = 25^\circ C, f = 1\text{ MHz}$	Fig. 5
E_C	Capacitance Stored Energy	119		μJ	$V_R = 800V, T_J = 25^\circ C$	Fig. 7

Note : This is a majority carrier diode, so there is no reverse recovery charge.

Thermal Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Unit	Note
$R_{\theta JC}$	Thermal Resistance from Junction to Case		0.45		$^\circ C/W$	Fig.8

Typical Performance

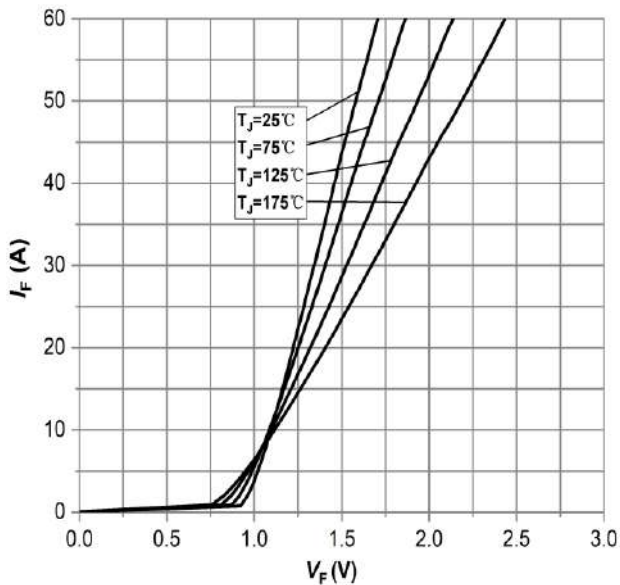


Figure 1: Forward Characteristics

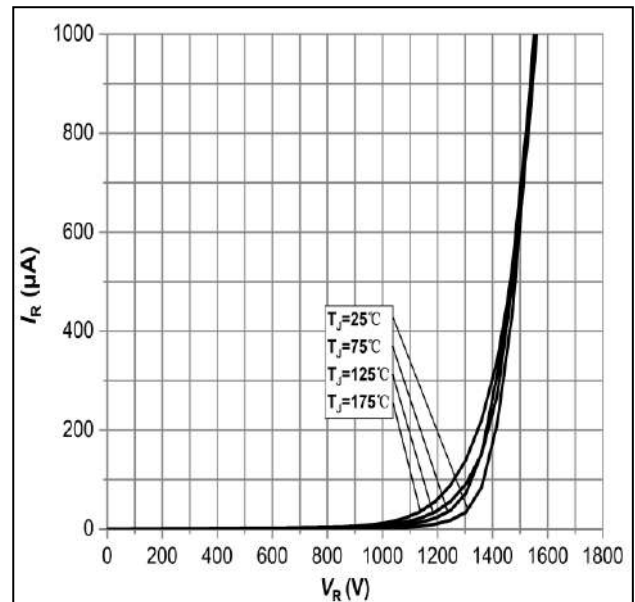


Figure 2: Reverse Characteristics

Typical Performance

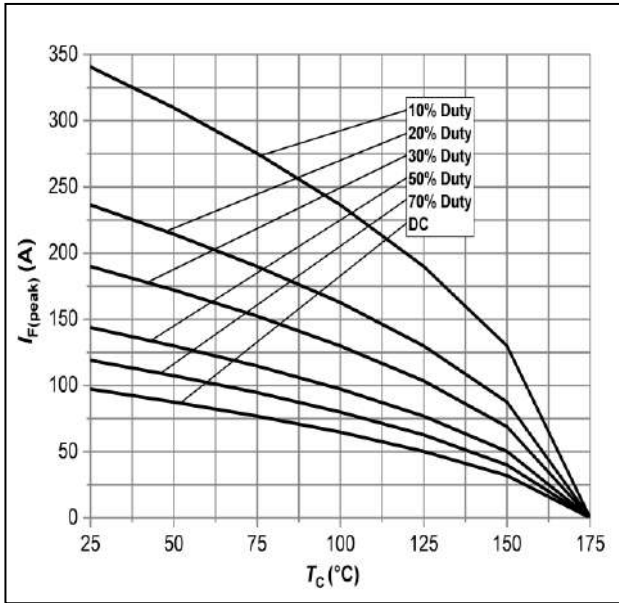


Figure 3: Current Derating

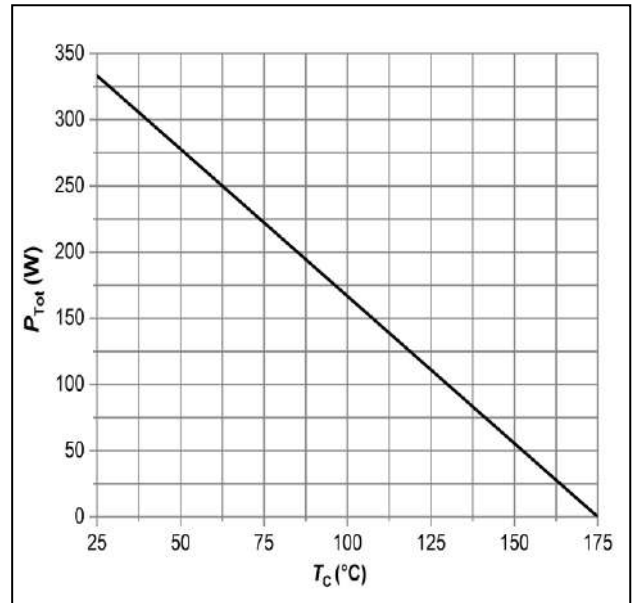


Figure 4: Power Derating

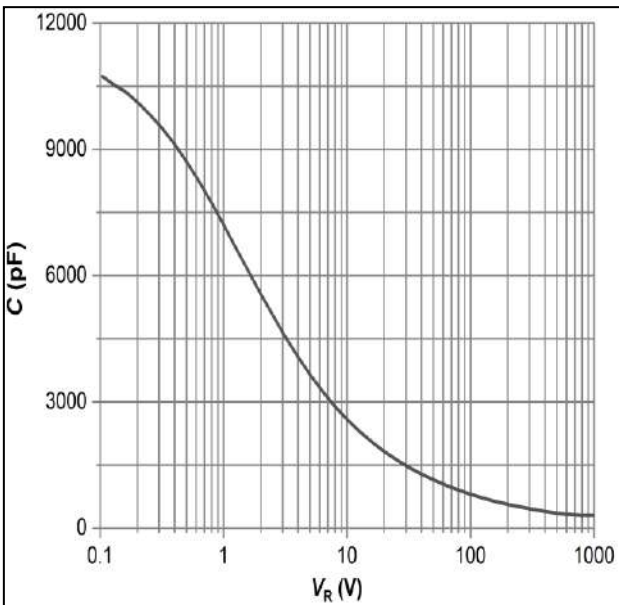


Figure 5: Capacitance vs. Reverse Voltage

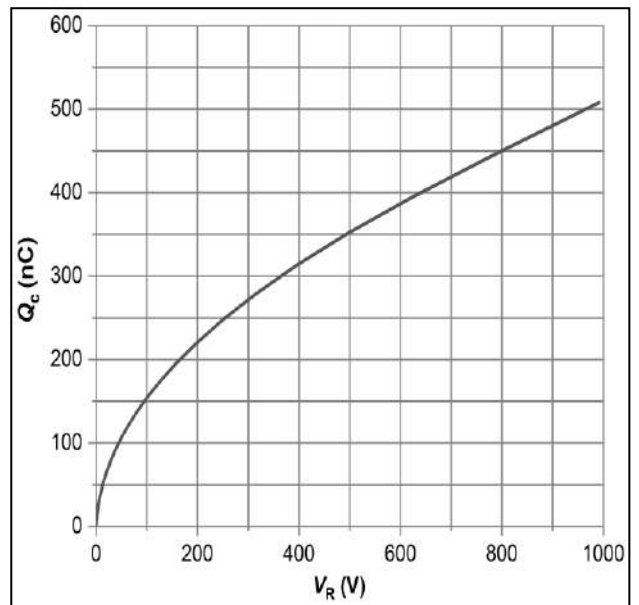


Figure 6: Total Capacitance Charge vs. Reverse Voltage

Typical Performance

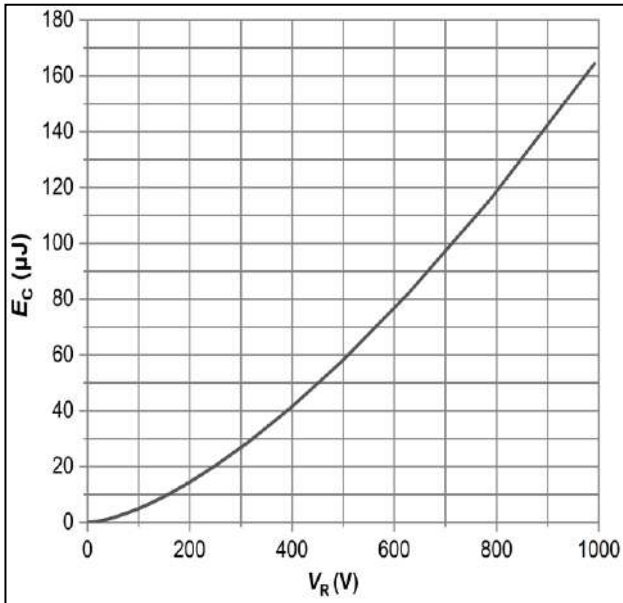


Figure 7: Typical Capacitance Stored Energy

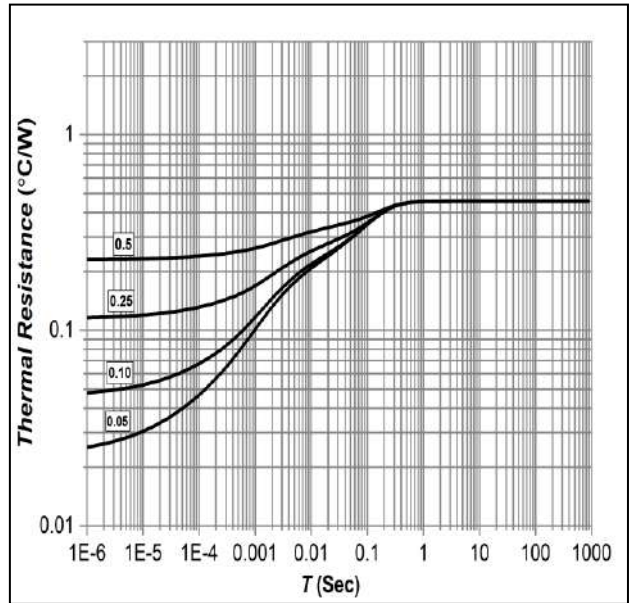
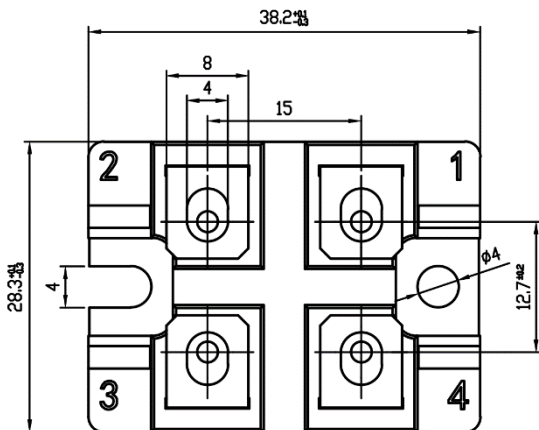
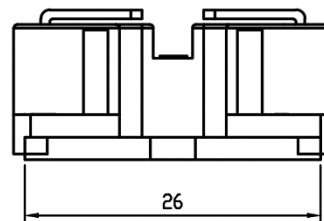
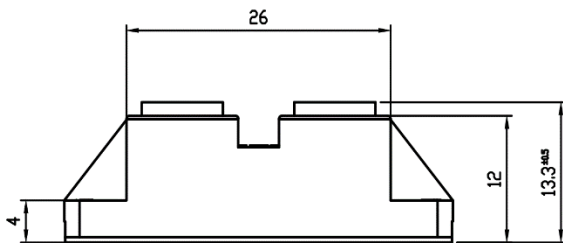


Figure 8: Transient Thermal Impedance

Package Dimensions

Package : SOT-227



All dimensions do not include mold flash or protrusions
All dimensions are in units mm

Revision History

Document Version	Description of Changes
RevX.0.1	Released

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